



FPF2C8P2NL07A F2, 3-phase, 3-level NPC module with Press-fit / NTC

General Description

Fairchild's new inverter modules provide low conduction and switching loss as well. And Press-Fit technology provides simple and reliable mounting. These modules are optimized for the applications such as solar inverter and UPS where a high efficiency and robust design is needed.

Electrical Features

- High Efficiency
- Low Conduction and Switching Losses
- Field Stop IGBT for Inner and Outer Switch
- STEALTHTM Diode for Path Diode
- Built-in NTC for Temperature Monitoring

Mechanical Features

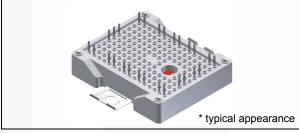
- Compact Size : F2 Package
- Press-fit Contact Technology
- Al₂O₃ Substrate with Low Thermal Resistance

Applications

- Solar Inverter
- UPS

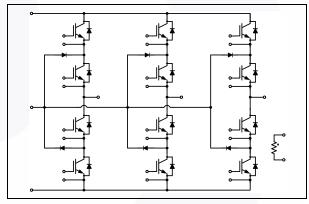
Related Materials

 AN-4167: Mounting Guideline for F1 / F2 Modules with Press-Fit Pins



Mar. 2015

Package Code: F2



Internal Circuit Diagram

Package Marking and Ordering Information

| Device | Device Marking | Package | Packing Type | Quantity / Tray |
|---------------|----------------|---------|--------------|-----------------|
| FPF2C8P2NL07A | FPF2C8P2NL07A | F2 | Tray | 14 |

| Symbol | Descr | Rating | Units | |
|--------------------|---------------------------------|---|---------------|----------|
| Outer IGBT | (Q1, Q4, Q5, Q8, Q9, Q12) | | | |
| V _{CES} | Collector-Emitter Voltage | 650 | V | |
| V _{GES} | Gate-Emitter Voltage | | ± 20 | V |
| I _C | Continuous Collector Current | @ T _C = 80 °C, T _{Jmax} = 175 °C | 30 | Α |
| I _{CM} | Pulsed Collector Current | limited by T _{Jmax} | 60 | A |
| P _D | Maximum Power Dissipation | @ T _C = 25 °C | 135 | W |
| TJ | Operating Junction Temperature | | - 40 to + 150 | °C |
| Inner IGBT | (Q2, Q3, Q6, Q7, Q10, Q11) | | | <u> </u> |
| V _{CES} | Collector-Emitter Voltage | | 650 | V |
| V _{GES} | Gate-Emitter Voltage | | ± 20 | V |
| I _C | Continuous Collector Current | @ T _C = 80 °C, T _{Jmax} = 175 °C | 50 | Α |
| I _{CM} | Pulsed Collector Current | limited by T _{Jmax} | 100 | A |
| P _D | Maximum Power Dissipation | @ T _C = 25 °C | 174 | W |
| TJ | Operating Junction Temperature | | - 40 to + 150 | °C |
| Outer - Inne | er IGBT Series Connection | | | |
| SCWT | Short Circuit Withstand Time | V _{DC} = 300 V, V _{GE} = 15 V T _C = 25 °C | 4 | μS |
| Diode | | | | |
| V _{RRM} | Peak Repetitive Reverse Voltage | | 650 | V |
| I _F | Continuous Forward Current | @ T _C = 80 °C, T _{Jmax} = 175 °C | 15 | A |
| I _{FM} | Maximum Forward Current | | 30 | A |
| P _D | Maximum Power Dissipation | @ T _C = 25 °C | 100 | W |
| TJ | Operating Junction Temperature | | - 40 to + 150 | °C |
| Module | | | | |
| T _{STG} | Storage Temperature | - 40 to + 125 | °C | |
| V _{ISO} | Isolation Voltage @ AC 1 min. | | 2500 | V |
| lsoMaterial | Internal Isolation Material | Al ₂ O ₃ | | |
| T _{MOUNT} | Mounting Torque | 2.0 to 5.0 | Nm | |
| Creepage | Terminal to Heat Sink | 11.5 | mm | |
| | Terminal to Terminal | 6.3 | mm | |
| Clearance | Terminal to Heat Sink | 10.0 | mm | |
| | Terminal to Terminal | 5.0 | mm | |

2